

ABSTRACT OF THE DISCLOSURE

A semiconductor device comprises a semiconductor substrate; a first insulation layer formed on the semiconductor substrate; a semiconductor layer insulated
5 from the semiconductor substrate by the insulation layer; a source region of a first conduction type and a drain region of the first conduction type formed in the semiconductor layer; a body region of a second conduction type formed in the semiconductor layer
10 between the source region and the drain region, said body region being capable of storing data by accumulating or releasing electric charge; a second insulation layer formed on the body region; a word line formed on the second insulation layer and insulated from
15 the body region by the second insulation layer; and a bit line electrically connected to the drain region, wherein the area of the body region in contact with the second insulation layer is larger than the area thereof in contact with the first insulation layer.